



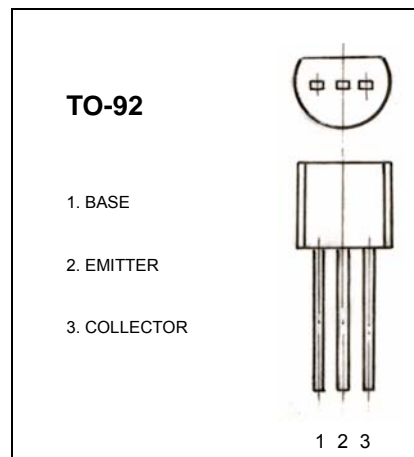
2SC2216 TRANSISTOR (NPN)

FEATURES

Amplifier dissipation NPN Silicon

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	50	V
V _{CEO}	Collector-Emitter Voltage	45	V
V _{EBO}	Emitter-Base Voltage	4	V
I _C	Collector Current -Continuous	50	mA
P _C	Collector Dissipation	300	mW
T _J	Junction Temperature	125	°C
T _{stg}	Storage Temperature	-55-125	°C



ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 100μA, I _E =0	50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 10 mA, I _B =0	45			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 100μA, I _C =0	4			V
Collector cut-off current	I _{CBO}	V _{CB} =50 V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 3 V, I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =12.5V, I _C =12.5 mA	40		140	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 15mA, I _B =1.5 mA			0.2	V
Bass-emitter saturation voltage	V _{BE(sat)}	I _C = 15mA, I _B =1.5 mA			1.5	V
Transition frequency	f _T	V _{CE} =12.5 V, I _C =12.5mA	300			MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=30MHz			2.0	pF